FEI Helios NanoLab 460F1
FIB operational guide
AggieFab
Texas A&M University

Contents

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Scope and Safety

- SCOPE
  - The purpose of this document is to describe requirements and basic operating instructions for the FEI Helios SEM/FIB System. The use of this tool is limited to approved processes only.
- SAFETY
  - Be sure that you are trained and signed off to use this equipment.
  - Be sure to keep all doors and protective shields in place before operating this equipment.
  - Use care when operating around high voltage or high current.
  - If you are unsure about any procedure or indication while operating this equipment be sure to contact a staff member or trainer for assistance.

Beginning your session

Note:
- Always check the stage in quad 4 on the screen when loading/unloading your samples.
- Please contact staff for ferromagnetic powers/particles or small samples.
- For ferromagnetic samples, place your sample securely on the stub so that samples will not hit the objective lens.

Starting your session
1. Start iLab.
2. Log in to the user software
3. Load your sample
    1. Check the height of your sample (pictures on next slide)
    2. Load samples (next slide)
    3. Wait until the stage transfers to the loading/unloading chamber
    4. Release the stage: 'Release' button
    5. Pick up the stage, load your sample, and place the stage back on the stage holder
    6. Click 'Load' button
    7. Wait until the stage transfer is completed
4. Take a Navigation picture
    1. In the menu, 'stage' – '**take nav-Cam Photo**'
    2. Explore the sample locations by clicking the specific locations in the picture at 3rd quad

Sample mount and loading/unloading

Sample stage: five slots

Max sample height

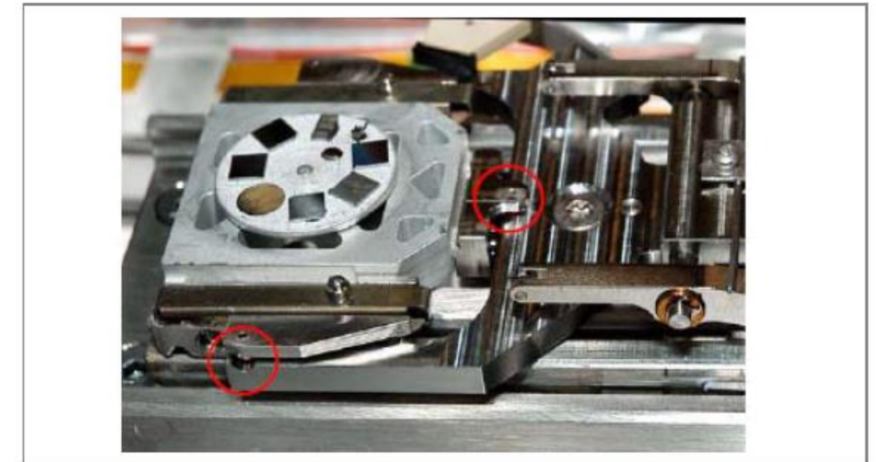
Unloading Sequence

1. Push the **Unload / Release** button to start the unloading sequence (lit is blinking). After finishing, the Loadlock is vented and the lid can be opened. Both buttons are enabled.
2. Open the lid, the **Clamp / Load** button becomes disabled. Push the **Unload / Release** button to release the carrier from the Loadlock arm.
3. Take the carrier out from the Loadlock arm.

Loading Sequence

1. Place the carrier on the Loadlock arm, making sure that all three alignment rubies are positioned properly. The **Clamp / Load** button becomes enabled (lit is on).

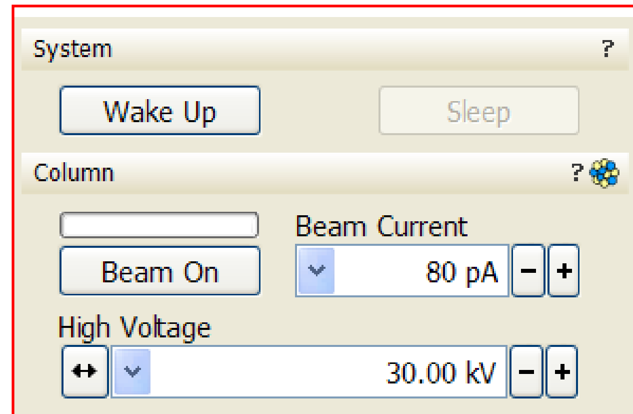
Figure 5-7 Alignment Rubies with Only Two Shown



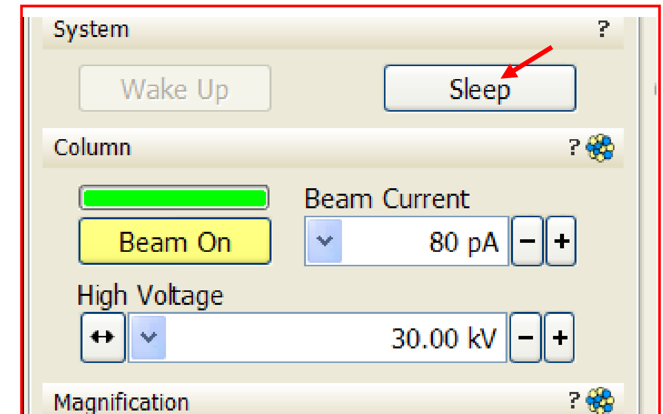
2. Close the lid and push the **Clamp / Load** button. The loading sequence starts (lit is blinking).

SEM USERS

Ion beam heater **OFF** state
Never click the **Wake Up** button
Sleep button should be grayed out.

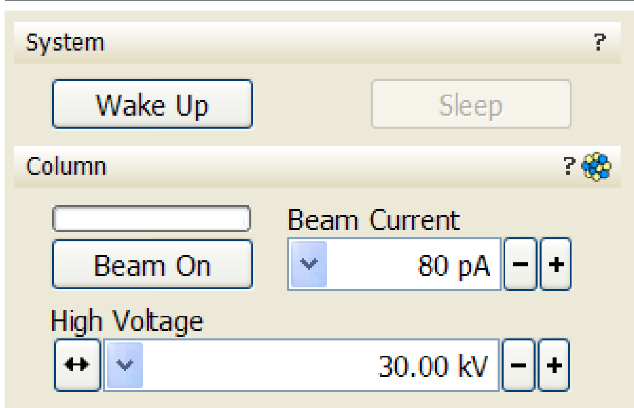


Ion beam **ON** state
If you see the **Sleep** button is activated, please click it to deactivate it

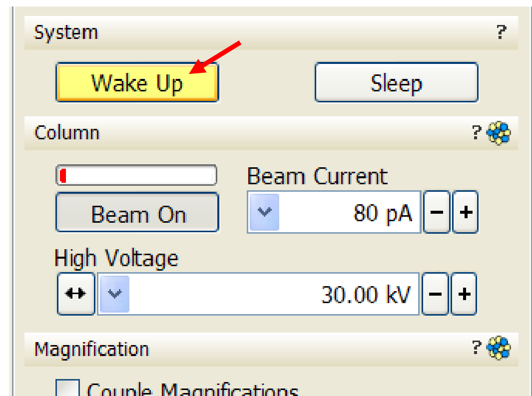


FIB USERS

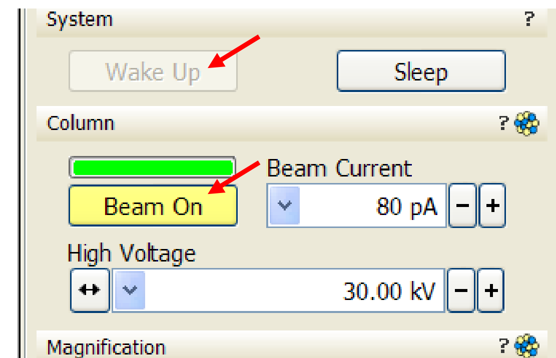
Not operating state: FIB not using
→ Ga ion source heater off
→ Ga ion beam not scanning



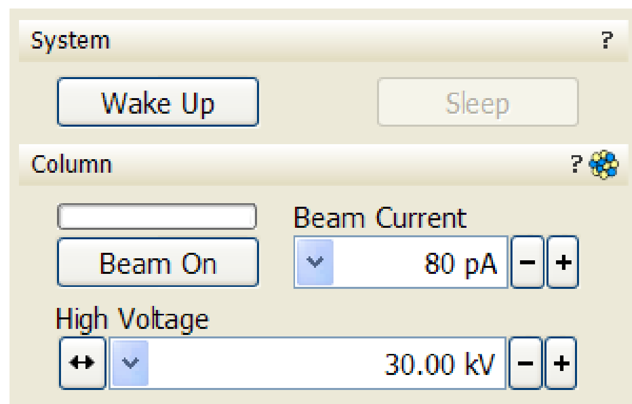
Heater on by click Wake Up
→ start to consume ion source
→ Ion beam yet to start to scan



Ga+ source completely heated up - operational
Ion beam scan by click Beam On
Good to go for FIB



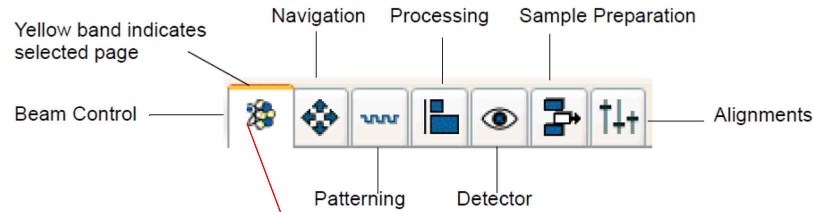
When FIB is finished,
1) Click 'Sleep'
2) Click 'Beam On'



Sleep button deactivated

Start Electron beam

Pages Toolbar



'**Reduced Area**'
icon

'**Pause**' icon

Beam control page

Turning e-beam

1. Click 'Beam control' in the **Pages Toolbar**
2. Click 1st quad on the monitor screen
3. Select the voltage and current
   - Menu bar or
   - **'Beam Control page'**
4. Click the **Beam on** button under the **'Beam Control page'** tab
5. Unpause the screen using the '**Pause**' icon

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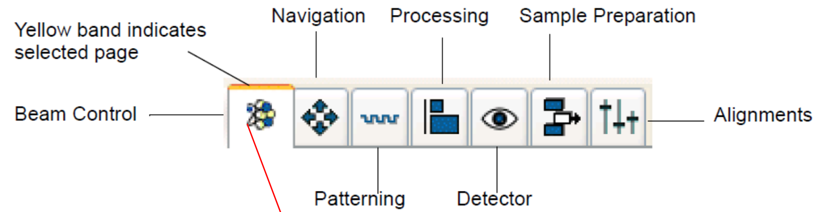
Start Ion beam (FIB users)



'**Reduced Area**' icon

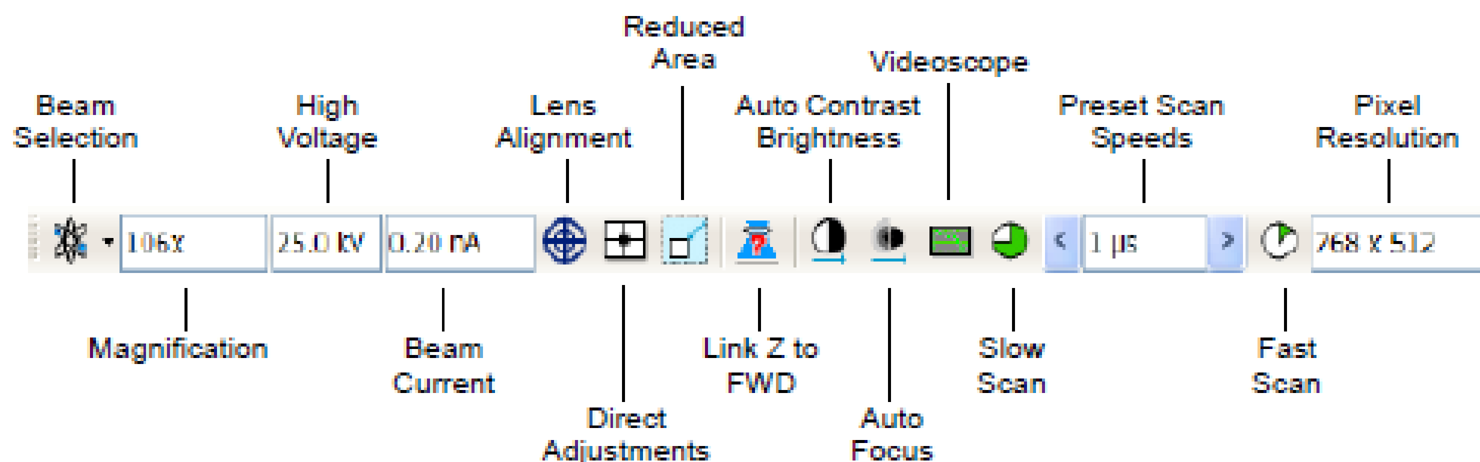
'**Pause**' icon

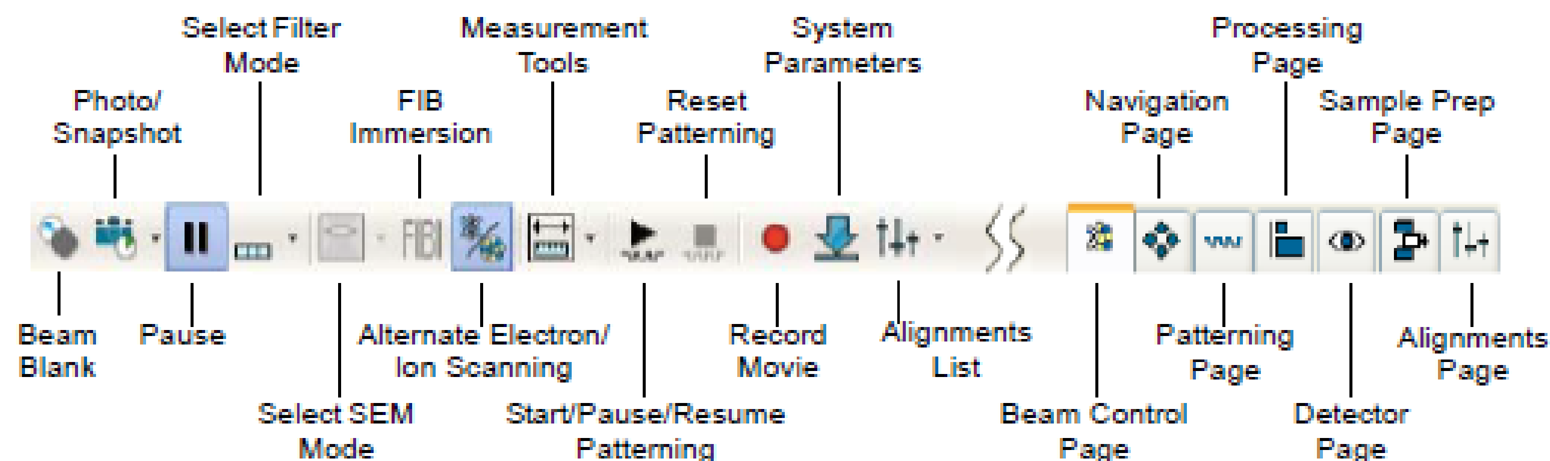
Beam control page

Turning Ion-beam

1. *Click the 2nd quad on the screen*
2. *Click the 'Wake Up' button (arrow)*
3. *Click the 'Beam On' button (arrow)*
4. *Leave the ion-beam as paused*
   - *The green pause symbol is shown left top screen*

Toolbar icons/menus





1. **Link Z to working distance**
   - Focus on the sample surface with SEM
   - Click 'Z to WD' icon: the icon changes its shape with green arrow.

2. **Set the working distance to 4 mm.**
   - Input 4 in the Z (Navigate page)
   - Click 'go to' button

3. **Find Eucentric height/point: the height of the stage where the specific point remains the same at tilt = 0 and 52**
   - Set magnification X1000
   - Find a recognizable feature, and center it under the yellow cross by moving the stage
   - Watching the feature, change the stage tilt to 10°. Using the Z control, bring the feature back under the cross
   - Repeat the previous step at 20° or 30°
   - Repeat at tilt = 52°

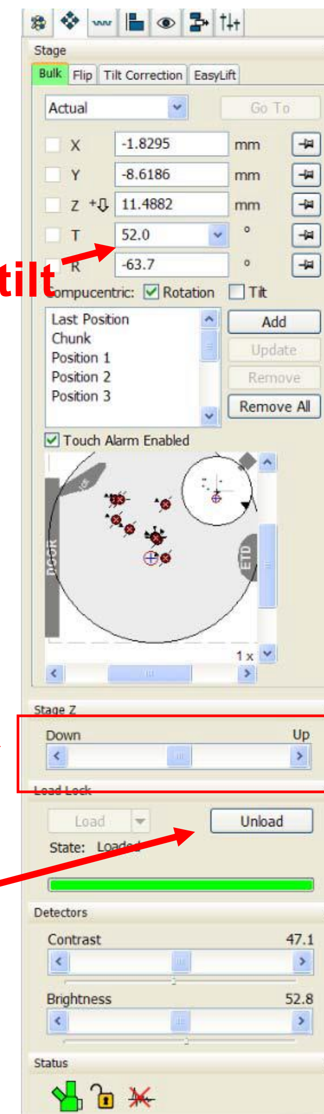
'Z to WD icon'

- **Red question mark**: The function is enabled and the link between Z and FWD is unknown. Use the function as soon as possible, after properly focusing the image.

- **Red circle**: The function is enabled. Z is roughly linked to FWD, but it needs correction. This could happen after changing the sample, focusing and linking Z to FWD at a long working distance (WD), and then moving the stage to a short WD. Focus the image carefully at a WD around 4 mm and use this function again.

- **Green double-ended arrow**: The function is still enabled and Z is properly linked to FWD. It is now safe to change the WD by setting a Z coordinate on the Stage page.

'Nevigate'



tilt

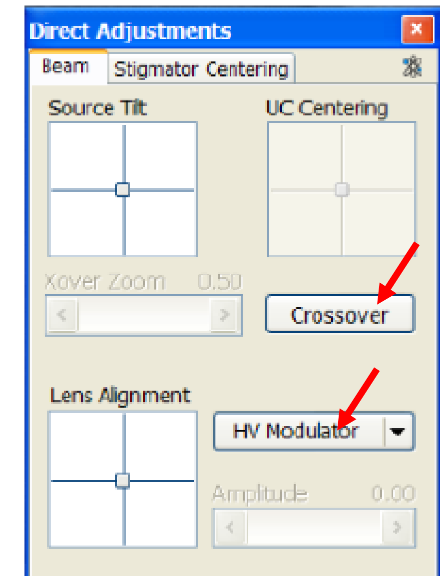
Stage move up/down

Load/Unload button

E-beam alignment

1. Focus on the surface with the magnification you will be doing operation.
2. Adjust stigma
3. Do the lens modulation
    1. Click ‘Direct Adjustments’ icon
    2. Click ‘Crossover’ button and center the beam
    3. Click ‘HV Modulator’ and make the image static by adjusting the horizontal and vertical lines. Click and drag the lines one by one.
4. Adjust focus and stigma again.

‘Direct Adjustments’



For SEM USERS

do your job and move to the last slide to shutdown the system

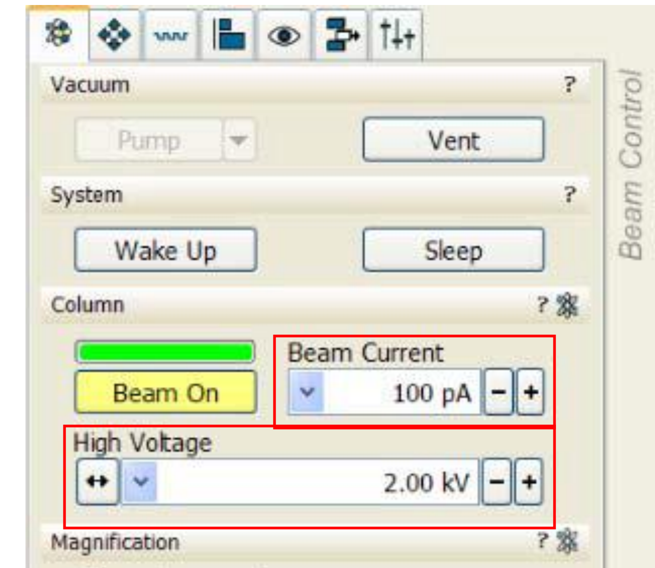
For FIB USERS

Go to next slide

FIB operation

Starting Ion-beam, tilt = 52°

1. Click 2nd quad on the screen
2. The Ga ion source was activated previously by clicking the 'Wake Up' button.
3. Select the 'Beam Current' and 'High Voltage': those can be selected in the 'Beam control page' or in the menu bar.
4. Before scanning I-beam, adjust the magnification.
5. Once the 2nd quad is unpaused, the ion beam scans the sample area.
6. 'Shift' key + 'mouse left drag' is used to shift the I-beam image to align it with the SEM image.
7. Adjust focus and stigma



Aperture		use
1.1	pA	High resolution imaging
7.7	pA	High resolution imaging
24	pA	High resolution imaging, small cross section cleaning
40	pA	General resolution imaging, cross section cleaning
80	pA	General resolution imaging, cross section cleaning
230	pA	Imaging, cross-section cleaning
430	pA	Cross-section cleaning
790	pA	Medium bulk milling or large cross-section cleaning
2.5	nA	Large cross-section cleaning
9.3	nA	Rough bulk milling for large cross-sections
21	nA	Extremely rough bulk milling for large cross-sections
47	nA	Extremely rough bulk milling for large cross-sections
65	nA	Extremely rough bulk milling for large cross-sections

Patterning tap (1/2)

1. Select a pattern from the Pattern Selector and draw a pattern in the active quad (1st quad: electrons, 2nd quad: ions).

2. Select a beam for patterning from the toolbar.
3. Enter a value in µm as the depth in the Property Editor.
4. Select the milling aperture.
5. Focus and stigmate the beam on the area adjacent to the pattern.
6. Snapshot a single frame to confirm the pattern position.
8. Select **Patterning > Start Patterning** or click **Start Patterning** on the toolbar to begin milling.
9. **Pause, resume,** and **stop** patterning by clicking the corresponding buttons in the menu bar

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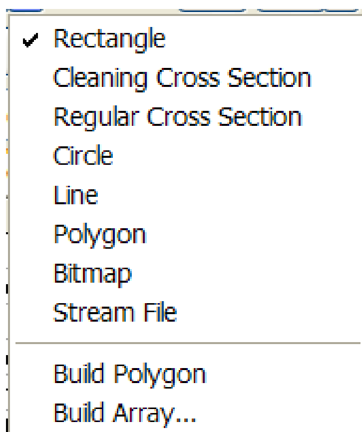
Patterning tap (2/2)

Pages Toolbar

Click drop down menu



Patterning Properties

Basic | Advanced | Progress | S. Mill

Name	Value
Application	
X size	0 µm
Y size	0 µm
Z size	0 **µm**
ScanDirection	Bottom To Top
DwellTime	0 s
Beam	Electron
Time	0 s
Beam Current	0 pA

Application: Name of the application. Clicking the value field produces a dropdown arrow and list of applications. The parameters for the selected application are automatically set for the subsequent properties.

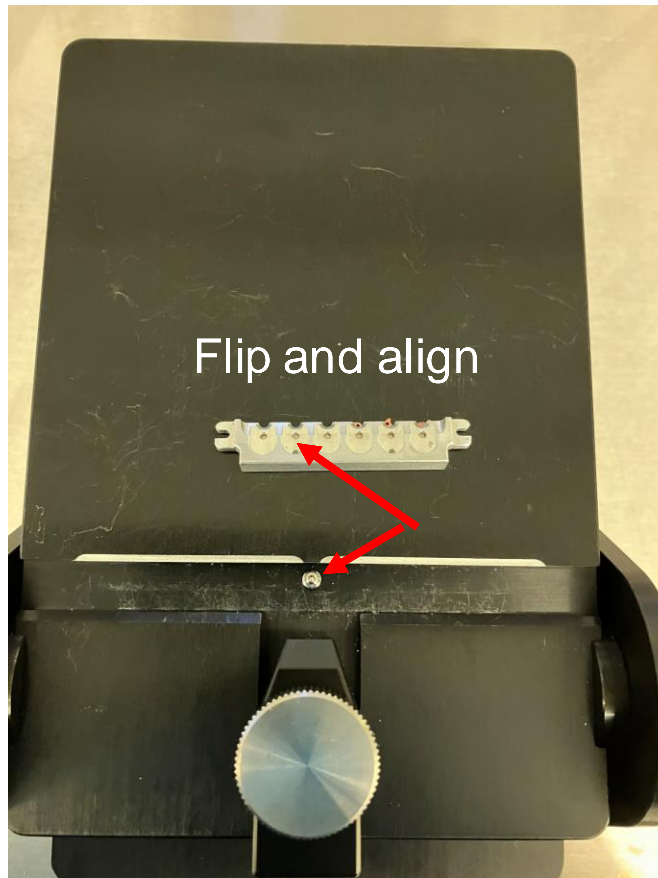
Scan Direction: Bottom to Top or Top to Bottom, etc.

Beam: The beam used for patterning

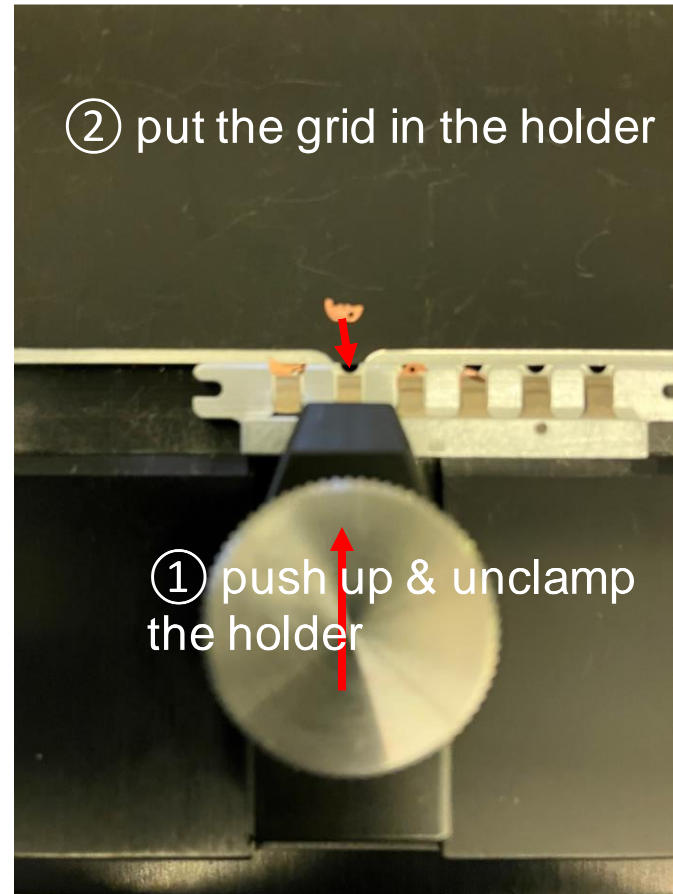
Beam Current: The amount of current striking the sample.

TEM lift out grid

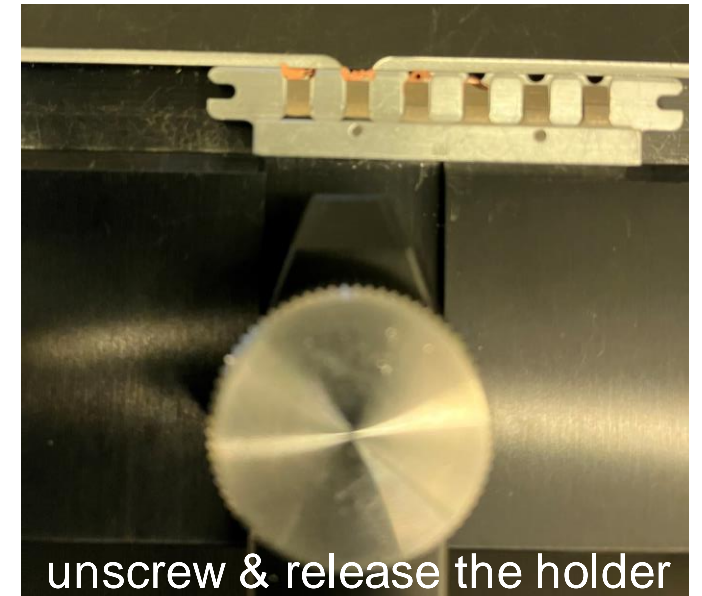
Placing TEM grid holder on the base



Clamping the grid

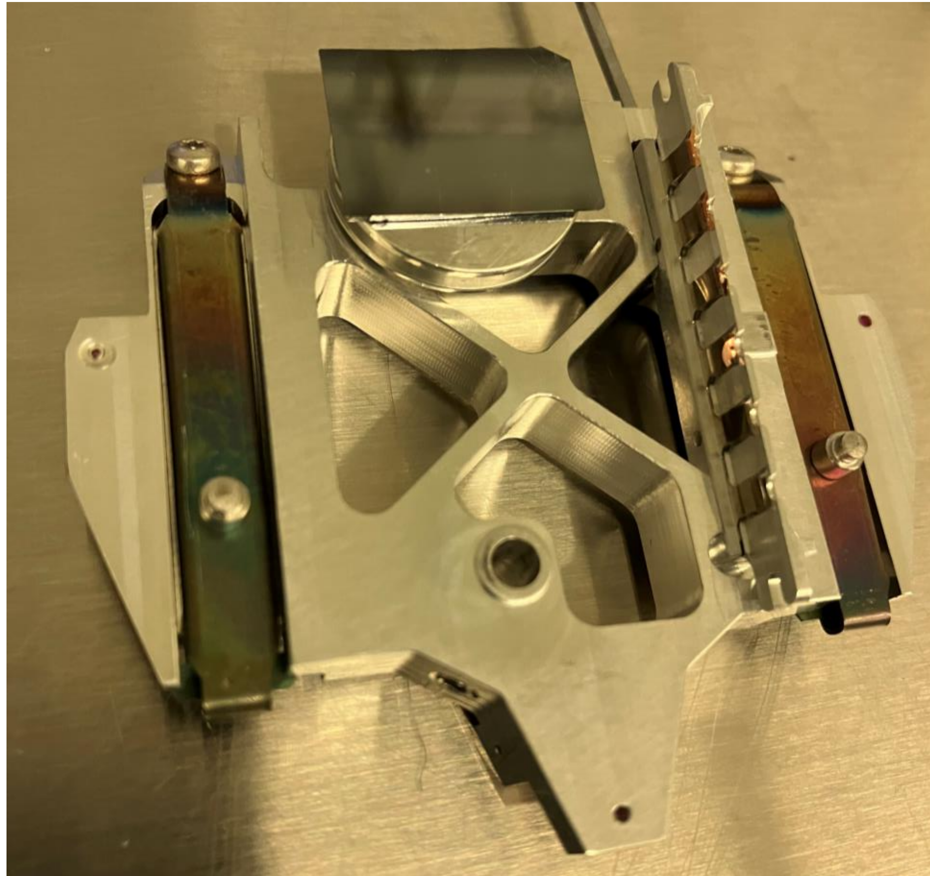


Releasing the holder



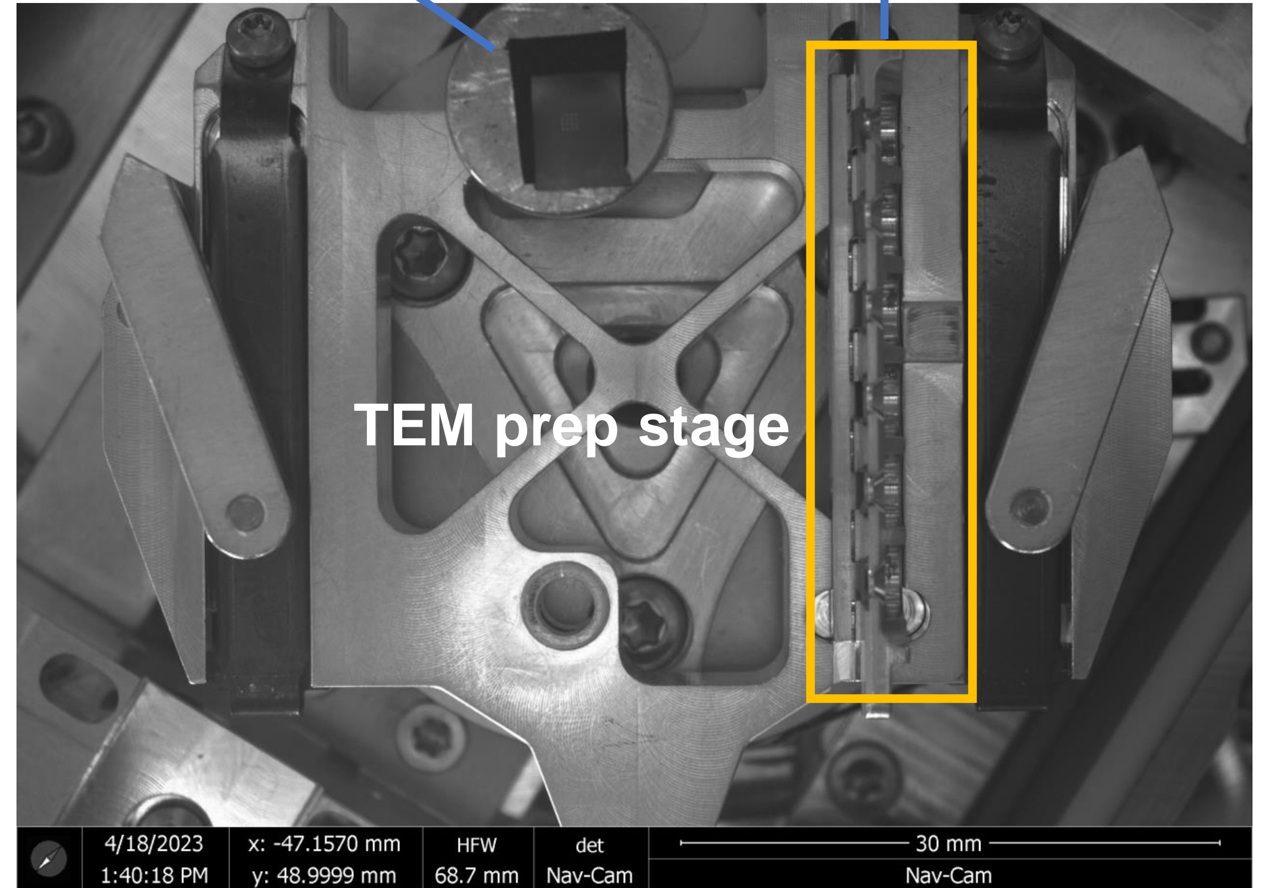
TEM sample holder

Dedicated stage for theTEM grid holder



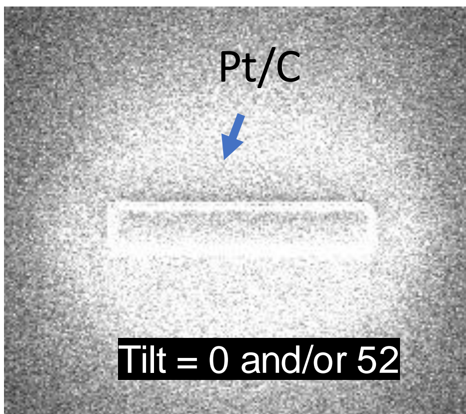
Sample

TEM grid holder

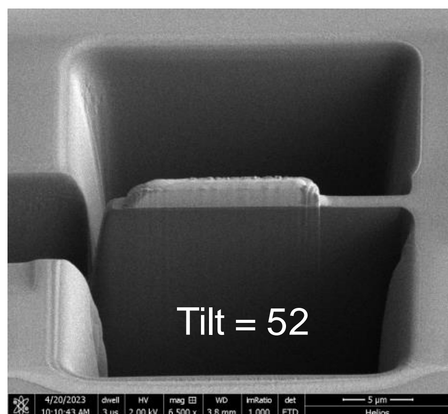


TEM sample lift out flow

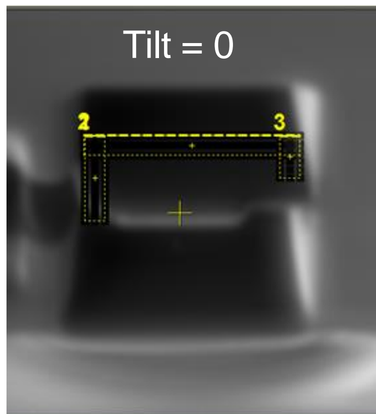
1. Cap deposition



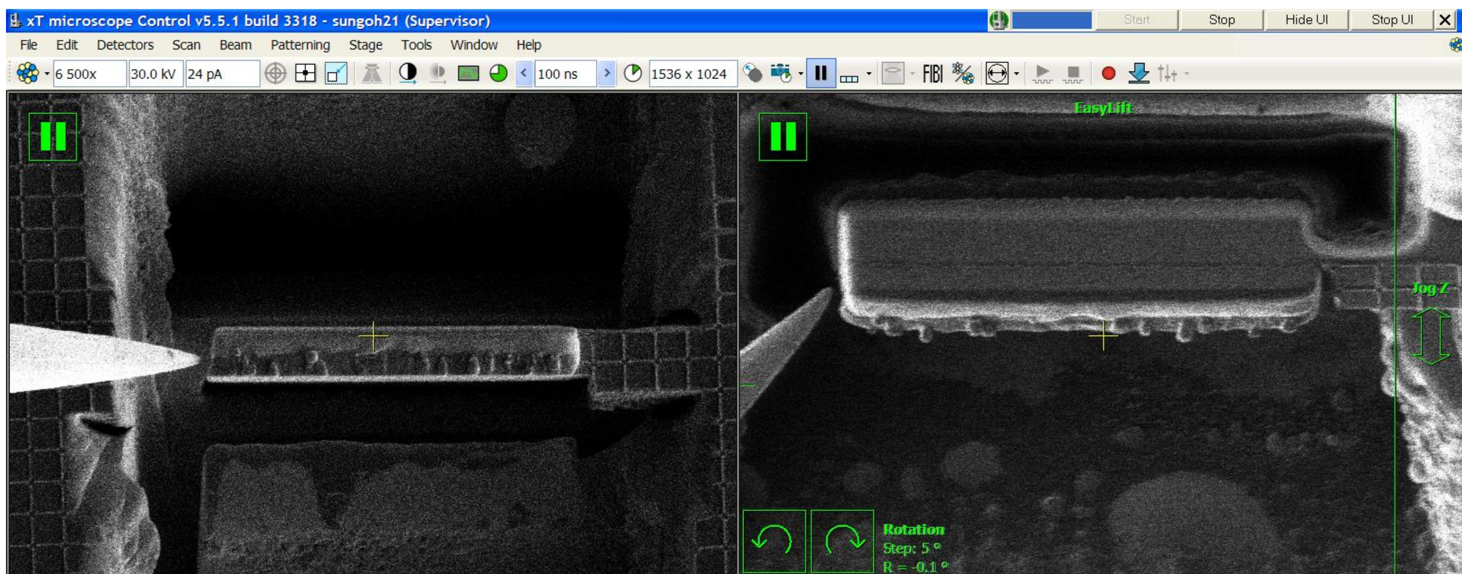
2. trenches



3. J cut



4. EasyLift: micromanipulator for sample handling



①

②

1 2 3 4 5 6

Stage ?

Bulk | Flip | Tilt Correction | EasyLift

Initialize

Retract

Jog Step

200 nm/s

Rotation Step

5 °

X, Y

Z

R = -0.1 °

Status: Ready

Park position

Update

Remove

Remove all

Navigation

④ Click 'Insert' or 'Retract' to insert and retract the tip.

③ select 'Park position'

⑤ manipulate the tip with the Jog

Cap deposition

⑤ Click 'start' - triangle

①

② draw pattern

③ Application: Pt_M

④ Insert the nozzle by click the green square for Pt

Name	Value
Application	Pt_M
X size	12.00 µm
Y size	1.50 µm
Z size	1.00 µm
ScanDirection	Bottom To Top
DwellTime	200.000 ns
Beam	Ion
Time	0:01:31
Beam Current	426.00 pA

In	Gas Type	Status	Flow
I	Pt	Ready	80.00%
I	C	Ready	80.00%
I	H2O	Ready	1.00%
I	XeF2	Off	1.00%
I	TEOS	Ready	10.00%

Cap deposition

1. Deposition for protecting the sample. Example: carbon and Pt deposition
    1. E-beam induced deposition, stage tilt = 0°
        1. In the 'Pattern' tab, draw a rectangle pattern in the 1st squd (SEM)
        2. In the '*Application*', select 'C e-dep surface'
        3. Insert gas injector needle: click the square for the gas you want to use
        4. Hit the start icon, triangle in the menu
        5. Low HV (<5kV) and high current (~26nA)
        6. Retract the gas nozzle
    2. I-beam induced deposition, stage tile = 52°
        1. Align the SEM and the FIB images using '*beam shift*'
        2. Click the 2nd sqad, and draw the pattern on the pattern
        3. Ex) carbon & Pt deposition, carbon deposition '*C_M*' and followed by Pt, '*Pt_dep*'
            1. Ion beam current depends on the size of patterns.
            2. Check focus, stigma, and shift when the beam current changes

Trenches

④ Click 'start' - triangle

①

② draw pattern

③ Application: Si or other materials

Name	Value
Application	none
X size	0 µm
Y size	0 µm
Z size	0 µm
ScanDirection	Bottom To Top
DwellTime	0 ps
Beam	Ion
Time	0 ps
Beam Current	0 pA

Trenches

1. Cross-section cuts – ‘Regular Cross Section 1’ top and bottom of the protection pattern
    1. Draw the cut patterns that are a couple microns wider than the protection pattern
    2. For bulk cuts, high current might be chosen. Adjust focus and stigma.
        1. Turn off the beam blaker, full screen, and then check the beam using the snapshot
            1. *‘Scan’ – ‘Spot’* mode. Select the point where the beam is pointing at.
            2. *‘Scan’ – ‘Beam Blank’.* I-beam exposure immediately.
            3. *‘Scan’ – ‘Full Frame’.*
        2. Put the gaps between the cut and the protection pattern according to the beam size
2. Cleaning cross section cut with two or three lower aperture (~20nA or less if needed)
    1. Application - ‘Si New’`

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Easy-Lift: micromanipulator

①

②

③ select 'Park position'

④ Click 'Insert To'

⑤

EasyLift insert needle

Do you want to insert the EasyLift needle to the position?

Park position | Cancel

TEM sample lift out

5. Lift out the sample

Tip-sample welding (Pt deposition)

cut

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TEM sample lift out - continued

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Place the sample on the grid

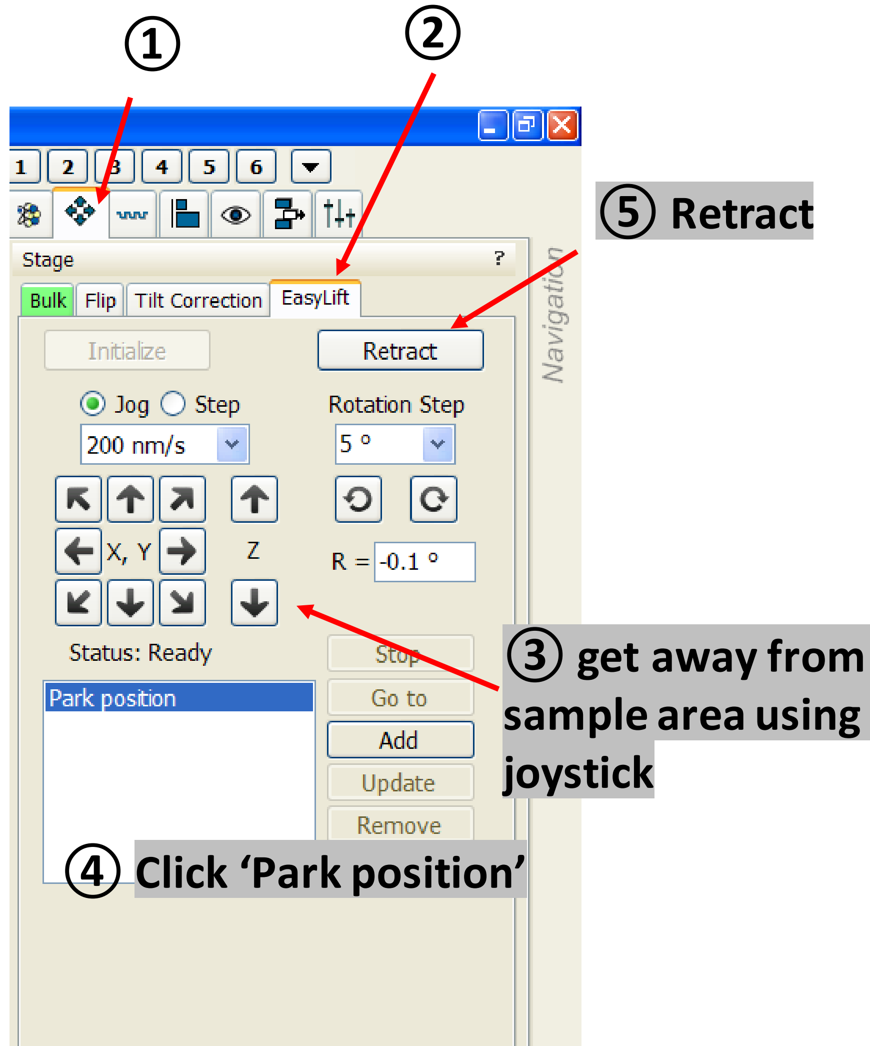
① welding

② cut

TEM grid:
The lamella can be oriented by rotating the stage or the micro-manipulator

Shutdown the system: FIB session

If you used the micromanipulator, Retract the micromanipulator



Finish the secession

1. Click the 'Pause' button to stop beams
2. Tun off the Ion-beam:
   - Click 2nd quad
   - Click '**Beam On**' AND '**Sleep**' button
3. Tun off the Electron-beam:
   - Click 1st quad
   - Click '**Beam On**'
4. Set tilt = 0
5. Unload your samples
6. Transfer the stage back to the main chamber:
   - wait until the stage comes back to the main chamber
   - Check visually through the CCD CAM at quad 4.
7. Log off the SEM/FIB software
   - File – log off
8. Log off iLab

Shutdown the system: SEM session

Finish the secession

1. Click the ‘Pause’ button to stop beams
2. Tun off the Electron-beam:
    - Click 1st quad
    - Click ‘**Beam On**’
3. Set tilt = 0
4. Unload your samples
5. Transfer the stage back to the main chamber:
    - wait until the stage comes back to the main chamber
    - Check visually through the CCD CAM at quad 4.
6. Log off the SEM/FIB software
    - File – log off
7. Log off iLab

Revision history

SIGNATURES AND REVISION HISTORY

1. Original author of this document: Dr. Sung Oh Woo
2. Original author Title or Role: Research Engineer
3. Date of original: 9/1/2022
4. Revision B notes: description of the LMIS handling is added

Approvals:

Technical Manager Signature:___*Sandra G Malhotra*

Date: __6/7/2024_________________________________

Revision	Author	Date
Original Issue	Sung Oh Woo	9/1/2022
Rev B	Sung Oh Woo	6/7/2024